

International **IR** Rectifier

1N6095
1N6096

SCHOTTKY RECTIFIER

25 Amp

Major Ratings and Characteristics

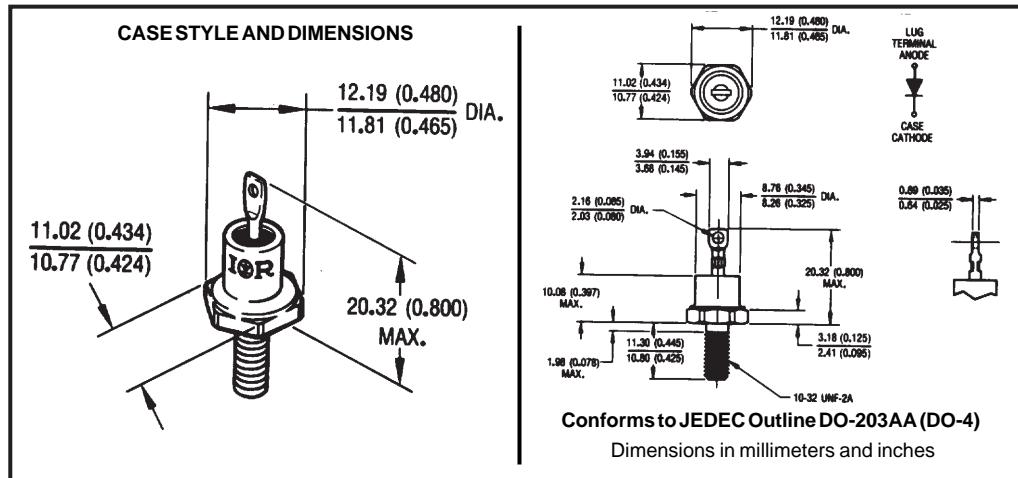
Characteristics	1N609.	Units
$I_{F(AV)}$ Rectangular waveform	25*	A
V_{RRM}	30/40*	V
I_{FSM} @ 60Hz	400*	A
V_F @ 80Apk, $T_J=70^\circ C$	0.86*	V
T_J range	-65 to 125*	°C

* JEDEC Registered Values

Description/Features

The 1N609. Schottky rectifier has been optimized for very low forward voltage drop, with moderate leakage. The proprietary barrier technology allows for reliable operation up to 125° C junction temperature. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

- 125° C T_J operation
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Hermetic packaging



1N6095, 1N6096

PD-2.331 rev. A 12/97

International
IR Rectifier

Voltage Ratings

Part number	1N6095	1N6096
V_R Max. DC Reverse Voltage (V)		
V_{RWM} Max. Working Peak Reverse Voltage (V)	30*	40*

Absolute Maximum Ratings

Parameters	1N609.	Units	Conditions
$I_{F(AV)}$ Max.AverageForwardCurrent See Fig. 5	25*	A	50%duty cycle @ $T_J = 105^\circ\text{C}$, rectangularwaveform
I_{FSM} Max.PeakOneCycleNon-Repetitive Surge Current See Fig. 7	400*	A	60Hzhalfwave,singlephase
E_{AS} Non-RepetitiveAvalancheEnergy	40	mJ	$T_J = 25^\circ\text{C}$, $I_{AS} = 6$ Amps, $L = 2.20$ mH
I_{AR} RepetitiveAvalancheCurrent	6	A	Currentdecayinglinearlytozero in 1 μsec Frequency limited by T_J max. $V_A = 1.5 \times V_R$ typical

Electrical Specifications

Parameters	1N609.	Units	Conditions		
V_{FM} Max. Forward Voltage Drop (1) See Fig. 1	0.86*	V	@ 80A	$T_J = 70^\circ\text{C}$	
I_{RM} Max. Reverse Leakage Current (1) See Fig. 2	60	mA	$T_J = 25^\circ\text{C}$	$V_R = \text{rated } V_R$	
	250*	mA	$T_J = 125^\circ\text{C}$		
C_T Typical Junction Capacitance	6000*	pF	$V_R = 1V_{DC}$, test signal range 100Khz to 1Mhz 25 °C		
L_S Typical Series Inductance	6.5	nH	Measured from top of terminal to mounting plane		
dv/dt Max. Voltage Rate of Change (Rated V_R)	10,000	V/ μs			

(1) Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications

Parameters	1N609.	Units	Conditions	
T_J Max.JunctionTemperatureRange	-65to125*	°C		
T_{stg} Max.StorageTemperatureRange	-65to125*	°C		
R_{thJC} Max.ThermalResistanceJunction toCase	2.0*	°C/W	DCoperation	See Fig. 4
R_{thCS} Typical ThermalResistance, Case to Heatsink	0.50	°C/W	Mountingsurface,smoothandgreased	
wt Approximate Weight	5.8(0.2)	g(oz.)		
T MountingTorque	Min.	14(12)	$\text{Kg}\cdot\text{cm}$ (lbf-in)	Non-lubricatedthreads
	Max.	23(20)		
Case Style	DO-203AA(DO-4)		JEDEC	

* JEDEC Registered Values

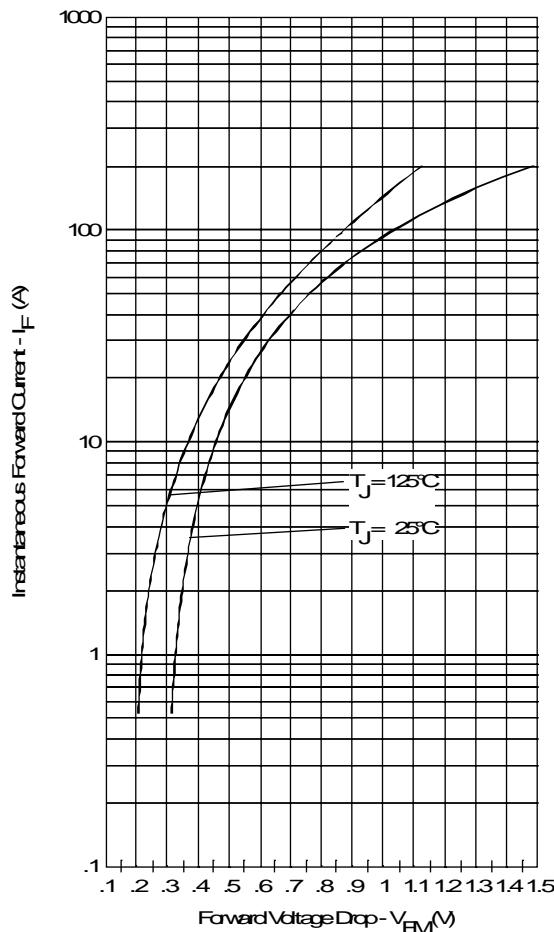


Fig. 1-Maximum Forward Voltage Drop Characteristics

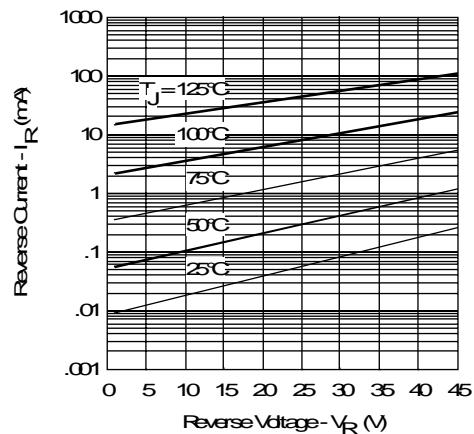


Fig. 2-Typical Values of Reverse Current Vs. Reverse Voltage

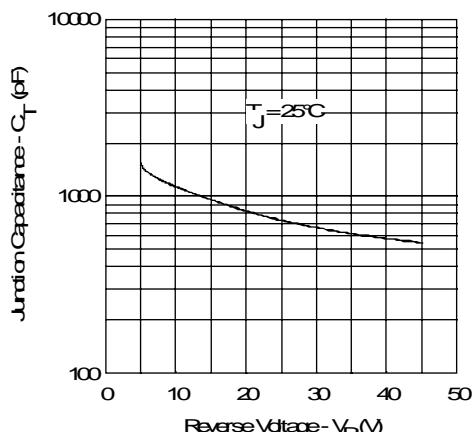


Fig. 3-Typical Junction Capacitance Vs. Reverse Voltage

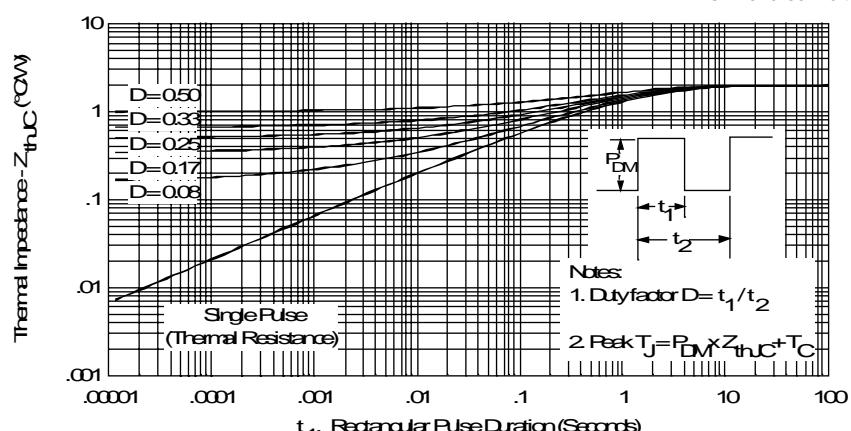


Fig. 4-Maximum Thermal Impedance Z_{thJC} Characteristics

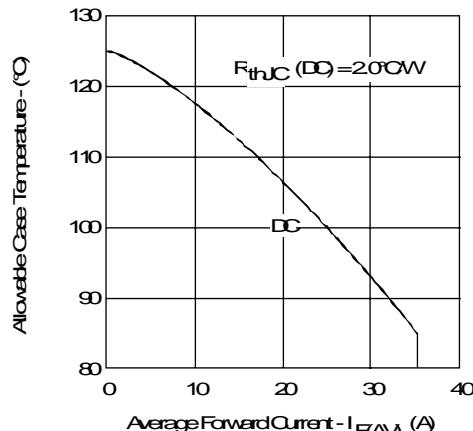


Fig.5-Maximum Allowable Case Temperature Vs. Average Forward Current

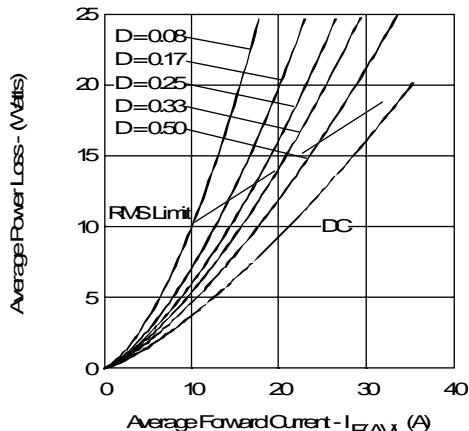


Fig.6-Forward Power Loss Characteristics

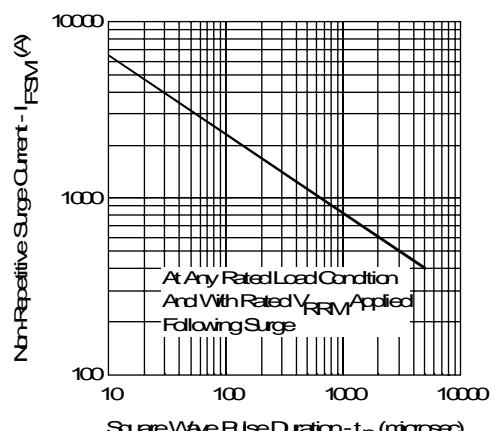


Fig.7-Maximum Non-Repetitive Surge Current

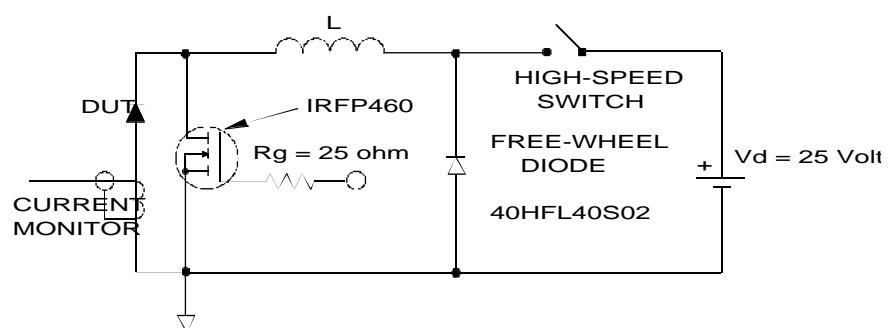


Fig.8-Unclamped Inductive Test Circuit